

Title (en)

LOW-E MATERIAL COMPRISING A THICK LAYER BASED ON SILICON OXIDE

Title (de)

LOW-E-MATERIAL MIT EINER DICKEN SCHICHT AUF BASIS VON SILICIUMOXID

Title (fr)

MATÉRIAU BAS ÉMISSIF COMPRENANT UNE COUCHE ÉPAISSE À BASE D'OXYDE DE SILICIUM

Publication

**EP 4149897 A1 20230322 (FR)**

Application

**EP 21732439 A 20210507**

Priority

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Abstract (en)

[origin: WO2021229165A1] The invention relates to material comprising a transparent substrate coated with a stack comprising at least one functional metal layer based on silver and at least two dielectric coatings, each dielectric coating comprising at least one dielectric layer, in such a way that each functional metal layer is positioned between two dielectric coatings, characterized in that the stack comprises a layer based on silicon oxide having a thickness of greater than or equal to 12 nm located directly in contact with the substrate.

IPC 8 full level

**C03C 17/36** (2006.01); **C23C 14/00** (2006.01)

CPC (source: EP US)

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Citation (search report)

See references of WO 2021229165A1

Designated contracting state (EPC)

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DOCDB simple family (application)

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